

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A light emitting device, comprising:

~~a GaN-based layer;~~

~~a high concentration GaN-based layer formed on the GaN-based layer;~~

a first conductive semiconductor layer;

an active layer formed on the first conductive semiconductor layer;

a second conductive semiconductor layer formed on the active layer;

a high concentration GaN-based semiconductor layer formed on the second conductive semiconductor layer;

a first metal-Ga compound layer formed on the high concentration GaN-based semiconductor layer;

a first metal layer formed on the first metal-Ga compound layer;

a third metal-Al compound layer formed on the first metal layer; and

a conductive oxidation preventive layer formed on the third metal-Al compound layer.

2-3. (Cancelled)

4. (Currently Amended) The light emitting device according to claim 1, wherein the second conductive semiconductor layer is a GaN-based layer is P-type or N-type GaN-based layer.

5. (Currently Amended) The light emitting device according to claim 1, wherein the first metal layer is of one selected from the group consisting of Cr, V and W.

6. (Cancelled)

7. (Currently Amended) The light emitting device according to claim 1, wherein the third metal is of one selected from the group consisting of Ni, Pt and Pd.

8. (Currently Amended) The light emitting device according to claim 1, wherein the third metal is of a metal or compound having a high reactivity with Al.

9. (Cancelled)

10. (Currently Amended) The light emitting device according to claim 1, wherein the conductive oxidation preventive layer is of Au, or is of a multi-metal or compound of two or more kinds containing Au.

11-52. (Cancelled)

53. (Currently Amended) The light emitting device according to claim 1, wherein the first conductive semiconductor layer is an N-type layer, and the second conductive semiconductor layer and the high concentration GaN-based semiconductor layer are P-type layers.

~~light device comprises an NP-type light emitting device or an NPN-type light emitting device.~~

54. (Currently Amended) The light emitting device according to claim 1, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.

55. (Currently Amended) The light emitting device according to claim 1, comprising a transparent electrode layer formed between the high concentration GaN-based semiconductor layer and the first metal-Ga compound layer.

56. (Currently Amended) The light emitting device according to claim 55, wherein the high concentration GaN-based layer is a P-type or N-type layer.

57. (Currently Amended) The light emitting device according to claim 55, wherein the first metal layer is of one selected from the group consisting of Cr, V and W, and the third metal is of one selected from the group consisting of Ni, Pt and Pd.

58. (New) The light emitting device according to claim 1, wherein the first metal-Ga compound layer, the first metal layer, the third metal-Al compound layer, and the conductive oxidation preventive layer form an electrode.

59. (New) The light emitting device according to claim 1, wherein the first conductive semiconductor layer comprises at least one of an Al material or an In material.

60. (New) The light emitting device according to claim 57, wherein the conductive oxidation preventive layer comprises one of Au, a multi-metal, and a compound of two or more kinds containing Au.

61. (New) The light emitting device according to claim 53, wherein the second conductive semiconductor layer comprises a vacancy structure.

62. (New) The light emitting device according to claim 1, wherein the third metal-Al compound layer is a metal layer.

63. (New) The light emitting device according to claim 1, wherein a high concentration GaN-based semiconductor layer comprises a carrier concentration of more than 10^{18}cm^{-3} .

64. (New) The light emitting device according to claim 1, wherein a high concentration GaN-based semiconductor layer comprises a carrier concentration more than a carrier concentration of the second type conductive semiconductor layer.